

Description

The AU1221P0 is a 12V bi-directional TVS diode, utilizing leading monolithic silicon technology to provide fast response time and low ESD clamping voltage, making this device an ideal solution for protecting voltage sensitive data and power line. The AU1221P0 complies with the IEC 61000-4-2 (ESD) with ±30 kV air and ±30 kV contact discharge. It is assembled into an ultra-small lead-free DFN0603-2 package. The small size and high ESD surge protection make AU1221P0 an ideal choice to protect cell phone, digital cameras, audio players and many other portable applications.

Features

- · Protects one data or power line
- Ultra low leakage: nA level
- Operating voltage: 12V
- Low clamping voltage
- Complies with following standards:
 - IEC 61000-4-2 (ESD) immunity test
 Air discharge: ±30kV
 - Contact discharge: ±30kV IEC61000-4-5 (Lightning) 5A (8/20µs)
- RoHS Compliant

Mechanical Characteristics

- Package: DFN0603-2
- Case Material: "Green" Molding Compound.
- Terminal Connections: See Diagram Below
- Marking Information: See Below

Applications

- Cellular Handsets and Accessories
- Personal Digital Assistants
- Notebooks and Handhelds
- Portable Instrumentation
- Digital Cameras
- Peripherals
- Audio Players

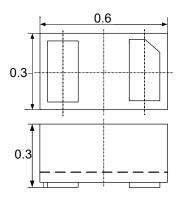
Marking Information

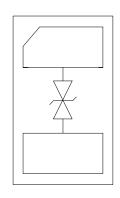


BH= Device Marking Code

Ordering Information

Dimensions and Pin Configuration





Package Dimensions Circuit and Pin Schematic

Part Number	Packaging	Reel Size
AU1221P0	10000/Tape & Reel	7 inch



Absolute Maximum Ratings (T_A=25°C unless otherwise specified)

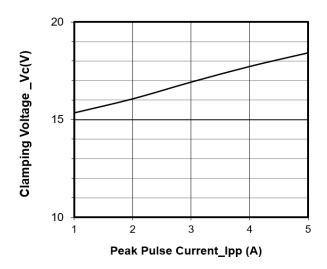
Parameter	Symbol	Value	Unit
Peak Pulse Power (8/20µs)	Ppk	100	W
Peak Pulse Current (8/20µs)	Ipp	5	Α
ESD per IEC 61000-4-2 (Air)	VESD	±30	kV
ESD per IEC 61000-4-2 (Contact)	VESD	±30	N.V
Operating Temperature Range	TJ	-55 to +125	°C
Storage Temperature Range	Tstg	-55 to +150	°C

Electrical Characteristics (T_A=25°C unless otherwise specified)

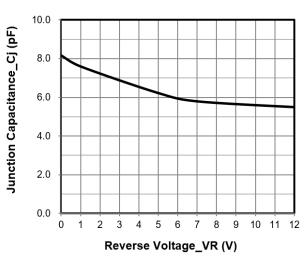
Parameter	Symbol	Min	Тур	Max	Unit	Test Condition
Reverse Working Voltage	VRWM			12	V	
Breakdown Voltage	VBR	13.3			V	IT = 1mA
Reverse Leakage Current	I _R			0. 2	μA	VRWM = 12V
Clamping Voltage	Vc			16	V	IPP = 1A (8 x 20µs pulse)
Clamping Voltage	Vc			20	V	IPP = 5A (8 x 20µs pulse)
Junction Capacitance	CJ		8	10	pF	VR = 0V, f = 1MHz



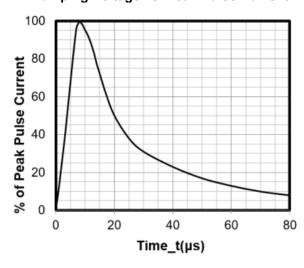
Typical Performance Characteristics (TA=25°C unless otherwise Specified)



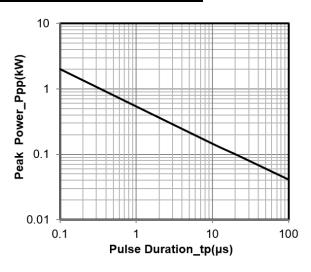
Junction Capacitance vs. Reverse Voltage



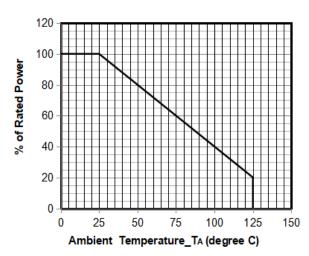
Clamping Voltage vs. Peak Pulse Current



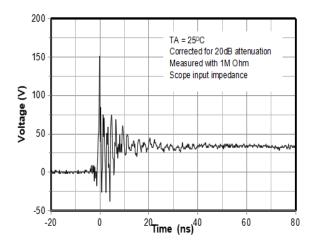
8 X 20µs Pulse Waveform



Peak Pulse Power vs. Pulse Time



Power Derating Curve

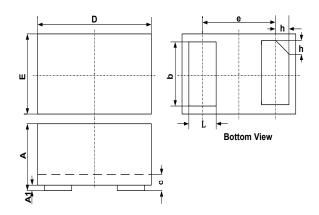


ESD Clamping Voltage 8 kV Contact per IEC61000-4-2

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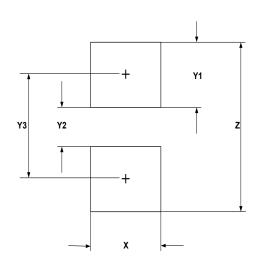


DFN0603-2 Package Outline Drawing



	DIMENSIONS			
	MILLIMETERS			
SYM	MIN	NOM	MAX	
Α	0.230		0.330	
A1	0.000	0.020	0.050	
b	0.215	0.245	0.275	
С	0.120	0.150	0.180	
D	0.550	0.600	0.650	
е		0.355 BS	C	
Е	0.250	0.300	0.350	
L	0.160	0.190	0.220	
h	0.079 BSC			

Suggested Land Pattern



CVM	DIMENSIONS			
SYM	MILLIMETERS	INCHES		
Х	0.30	0.012		
Y1	0.25	0.010		
Y2	0.15	0.006		
Y3	0.40	0.016		
Z	0.65	0.026		

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